

NIKON PRECISION INC.

Extension of 193 Immersion Lithography

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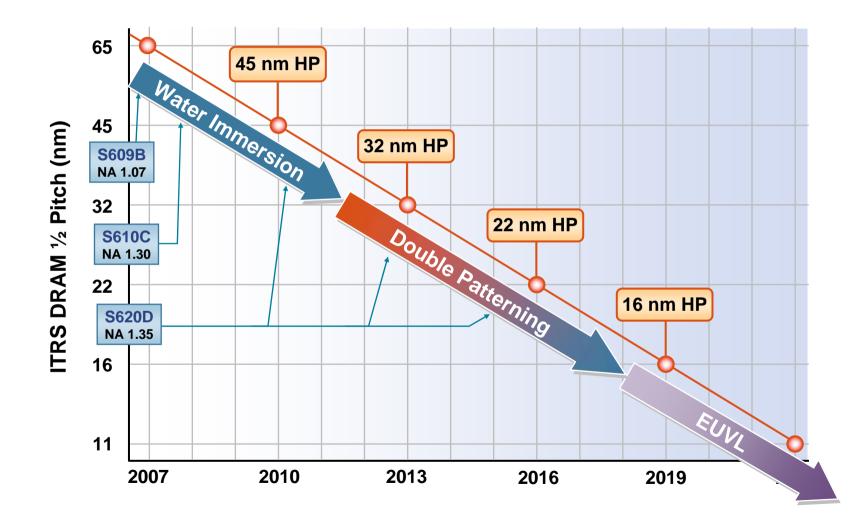
Overview



- EUV Status
- Bridging to EUV
- Scanner Requirements for DP
- NSR-S620D Performance

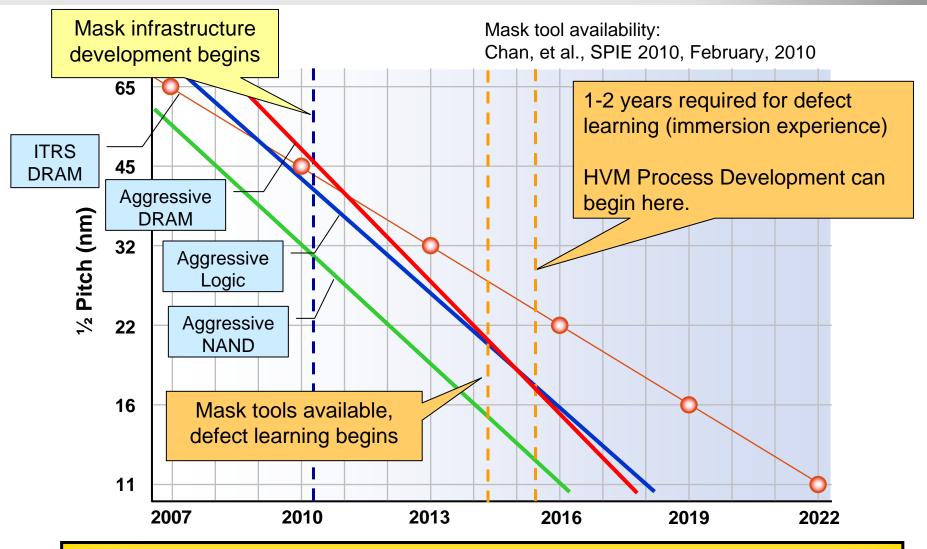
Lithography Technology Roadmap





EUV Infrastructure Schedule





Delays in infrastructure continue to push out adoption of EUV → increased cost and longer ROI for equipment makers

Extension of 193i Before EUV Arrives

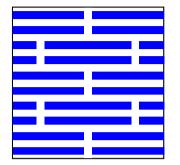


- Extend single patterning:
 - Source mask optimization and custom illumination
- Enable 32 nm half pitch and beyond
 - Spacer double patterning
 - Pitch splitting double patterning (LELE, LFLE, etc.)
 - Line cutting lithography

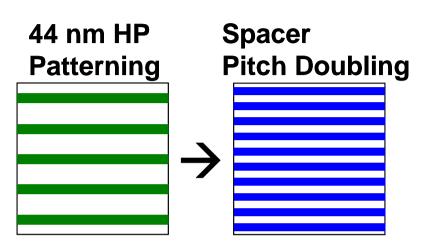
Tool makers need to support these schemes

Line Cutting Litho Concept





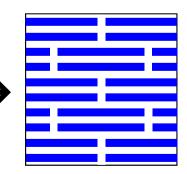
Target 22 nm SRAM Gate Cell



Cut Hole Patterning

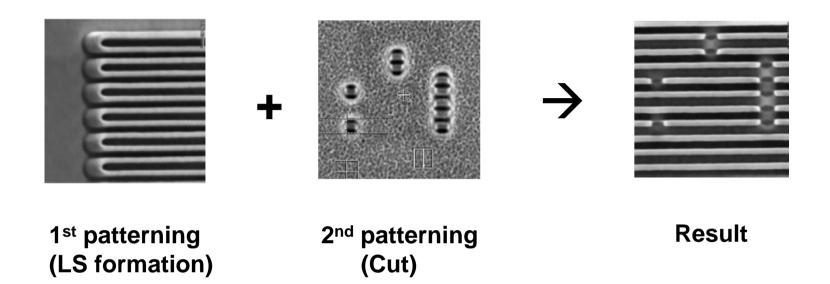
Hole Chemical Shrink





Line Cutting Lithography Concept





C. Bencher, et al., SPIE 72740G (2009)

Down to 19 nm half pitch can be achieved

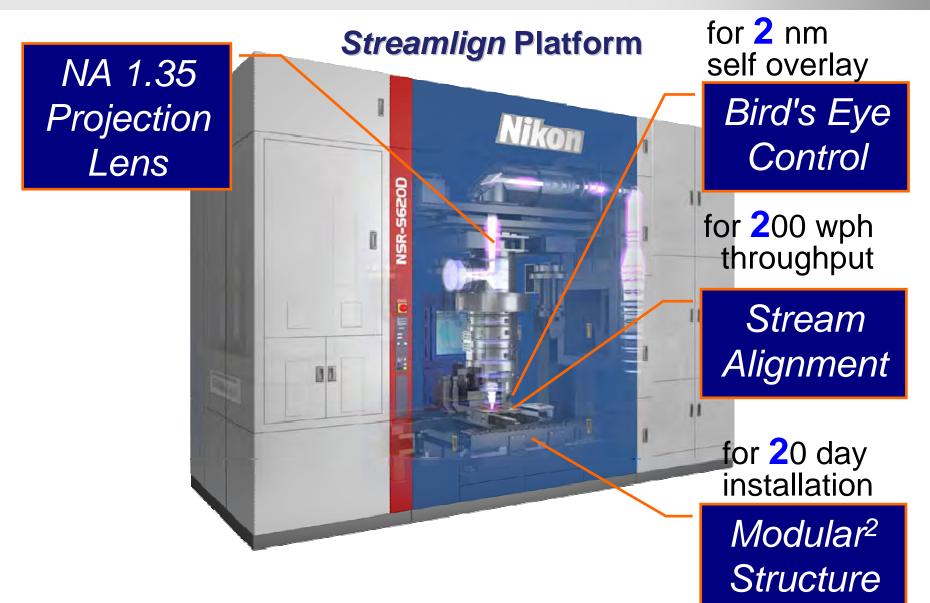
S620D – Enabling the Next Generation



- Enabling Superior Yield:
 - Overlay accuracy to enable DP
 - CD uniformity
- Enabling Affordable Lithography:
 - Reduced wafer overhead time
 - Maximum throughput
 - Low CoO via multi-generational use of the tool
- Enabling Rapid Production Ramps:
 - Faster installation
 - Optimal uptime
 - Platform to enable reuse

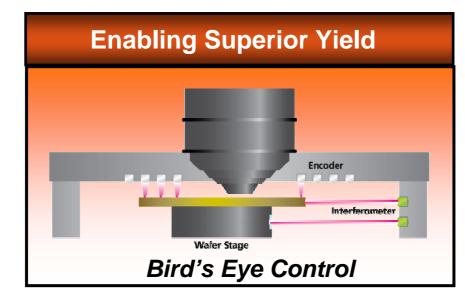
The NSR-S620D Challenge



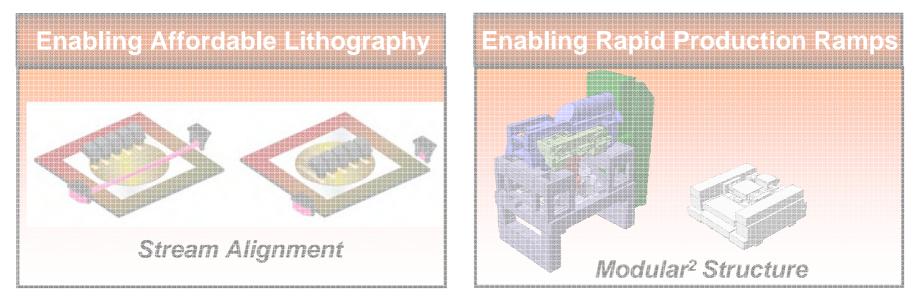


Bird's Eye Control





- Hybrid system uses laser encoders w/interferometers
- Dramatically improves accuracy and stability
- Targeting 2 nm overlay capabilities
- Superior focus control



Stream Alignment

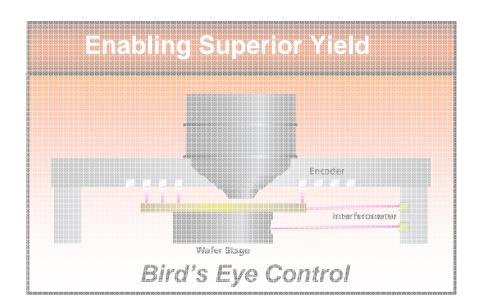


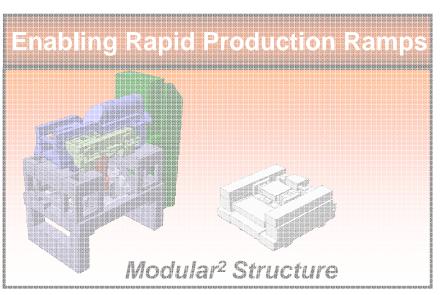
Enabling Affordable Lithography



Stream Alignment

- Five-Eye FIA
- Straight Line Autofocus
- Greatly reduced wafer overhead time
- Targeting throughput up to 200 wph

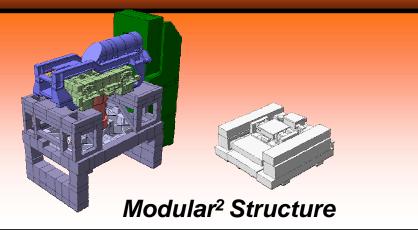




Modular² Structure

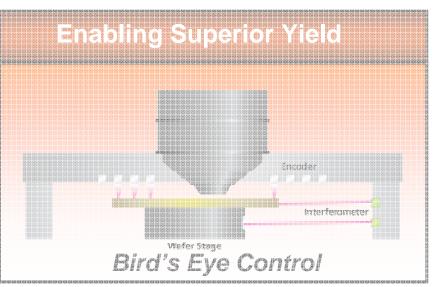


Enabling Rapid Production Ramps



- Faster installation 20 day target
- Simplified maintenance
- Optimal uptime
- Extendible platform to enable reuse





Scanner Requirements for DP



32 nm hp DP Budget

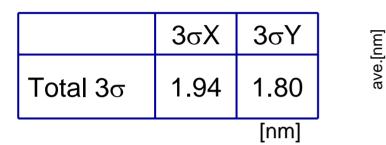
	Budget Spec	Line CDU	Space CDU
$\overline{L_1} - \overline{L_2}$	1.0 nm	2.9 nm	
$CDU(3\sigma)$	2.4		
OL $\overline{m_1} - \overline{m_2}$	0.5		3.3 nm
$OL(3\sigma)$	2.4		

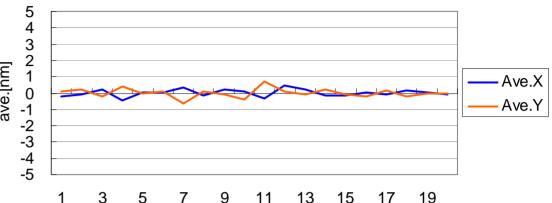
CD control and overlay are critical for **DP**

S620D Overlay Stability



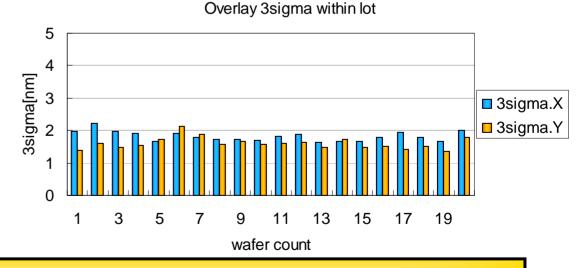
Overlay average within lot





20 wafers continuous exp.

 Common linear terms removed

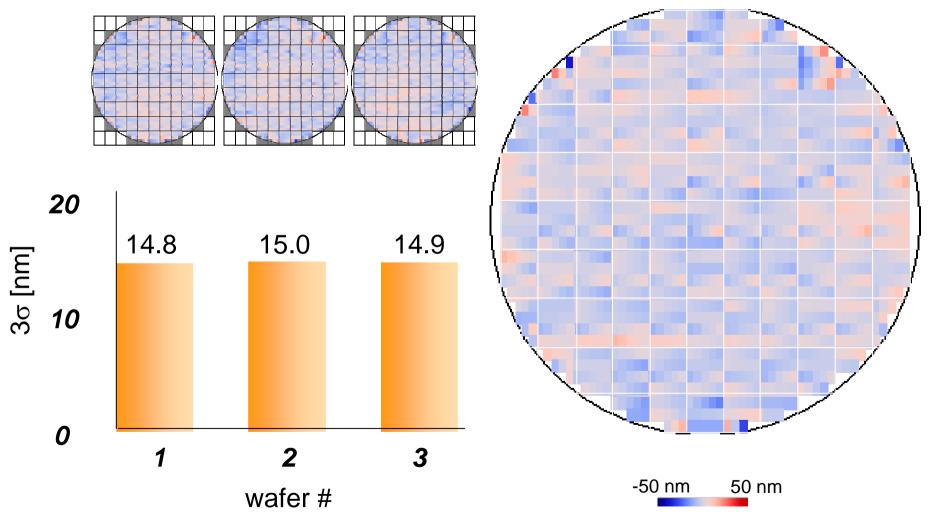


S620D meets overlay requirements for 32 nm hp DP

Focus Uniformity







Budget vs. S620D Data



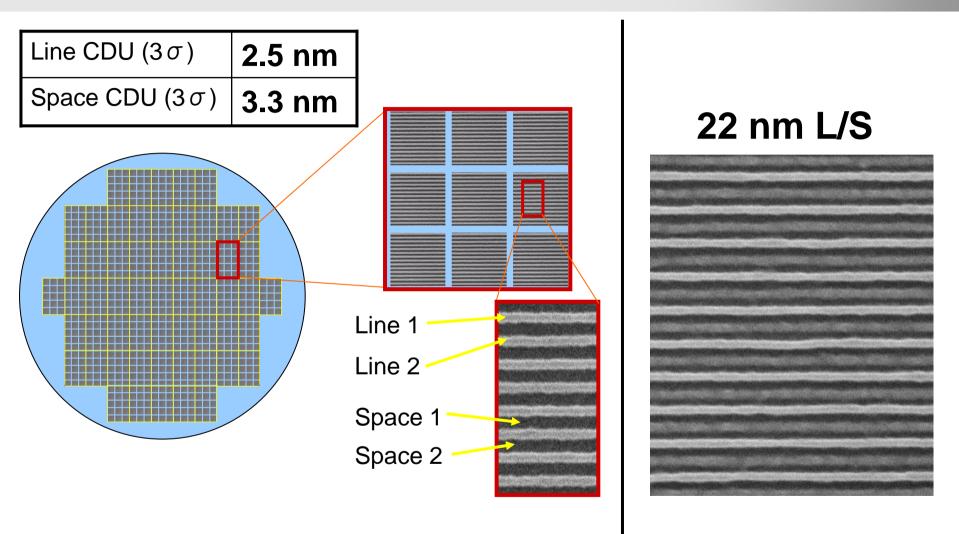
32 nm hp DP Budget and Actual Data

	Budget Spec	Line CDU	Space CDU
$\overline{L_1} - \overline{L_2}$	1.0 nm 1.1	2.9 nm	
ΔCD	2.4 2.1	2.5	
$\overline{m_1} - \overline{m_2}$	0.5 0.7		3.3 nm 3.3
ΔOL	2.4 1.9		

S620D data meet the budget requirement

S620D Overall Performance

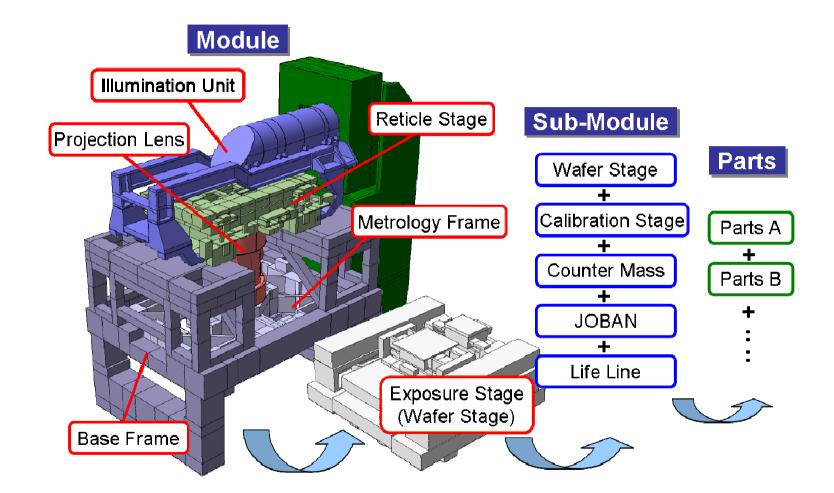




S620D enables pitch splitting DP

Extendible Platform for ArF Immersion





Modular² Structure allows multigenerational use

Summary



- The industry needs an interim solution for the 32 nm and 22 nm nodes, prior to the HVM development of EUV
- 193 immersion lithography will be extended by:
 - Source optimization and computational lithography
 - Double patterning
 - Multiple patterning and cutting lithography
- This places severe new requirements on a scanner for overlay and CD uniformity
- The Nikon S620D enables superior yield, affordable lithography, and rapid production ramps for 32 nm with extendibility to 22 nm



NSR-S620D ENABLING THE NEXT GENERATION